

PNP SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

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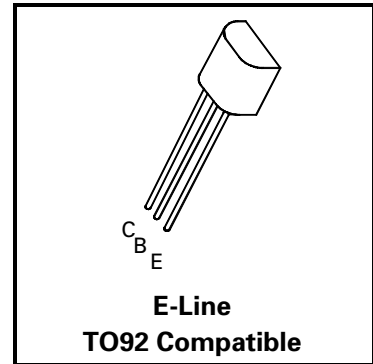
ZTX718

FEATURES

- * 6A Peak pulse current
- * Excellent h_{FE} characteristics up to 6A (pulsed)
- * low saturation voltage
- * I_C Cont 2.5A

APPLICATIONS

- * Power MOSFET gate driver in conjunction with complementary ZTX618



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-20	V
Collector-Emitter Voltage	V_{CEO}	-20	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-6	A
Continuous Collector Current	I_C	-2.5	A
Base Current	I_B	-500	mA
Practical Power Dissipation*	P_{totp}	1.5	W
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^{\circ}C$

* Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.

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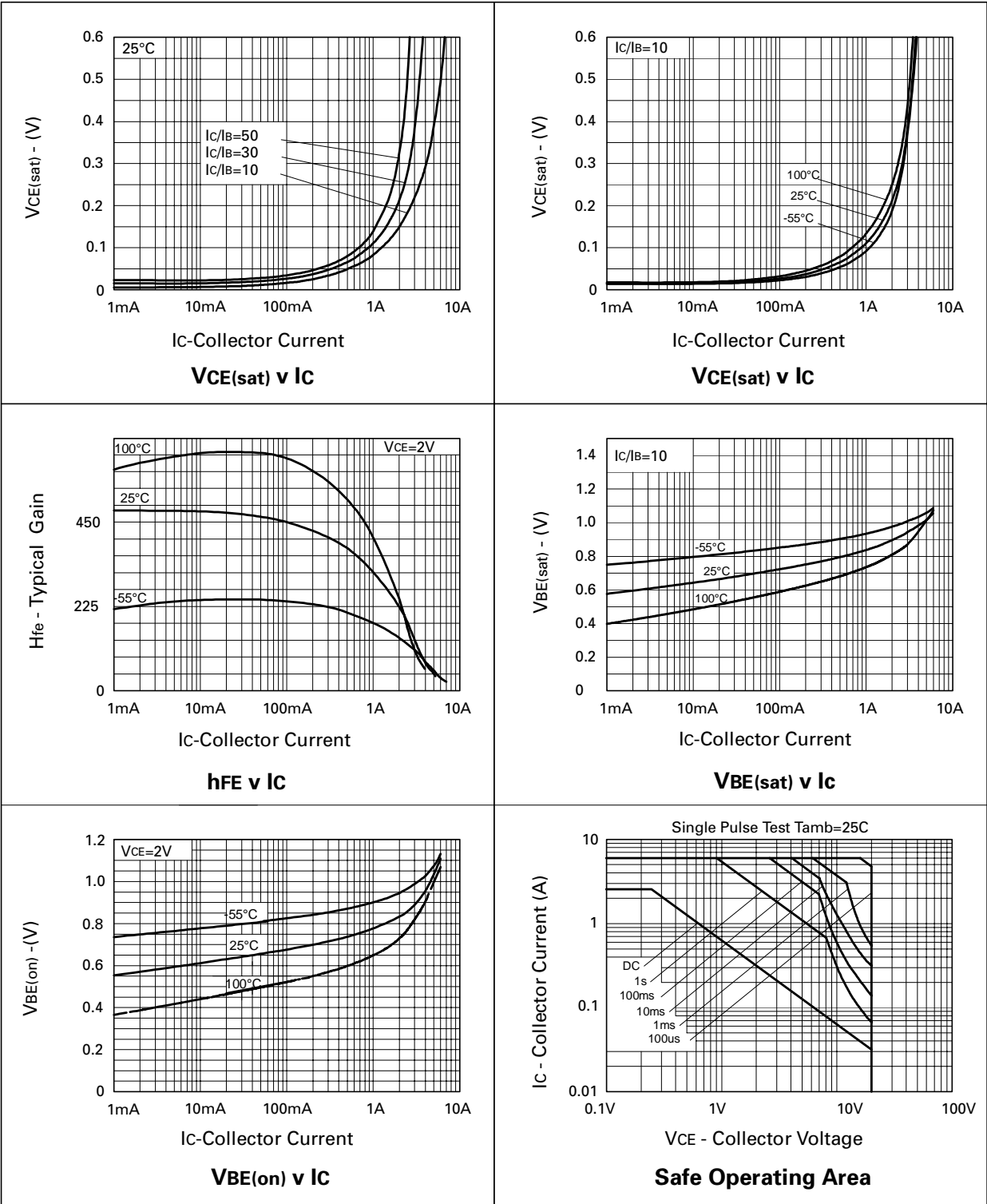
ELECTRIAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-20	-65		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-20	-55		V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-8.8		V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			-100	nA	$V_{CB} = -15\text{V}$
Emitter Cut-Off Current	I_{EBO}			-100	nA	$V_{EB} = -4\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			-100	nA	$V_{CES} = -15\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-16 -130 -145 -190	-40 -200 -220 -260	mV mV mV mV	$I_C = -0.1\text{A}, I_B = -10\text{mA}^*$ $I_C = -1\text{A}, I_B = -20\text{mA}^*$ $I_C = -1.5\text{A}, I_B = -50\text{mA}^*$ $I_C = -2.5\text{A}, I_B = -200\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.98	-1.1	V	$I_C = -2.5\text{A}, I_B = -200\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.85	-0.95	V	$I_C = -2.5\text{A}, V_{CE} = -2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	300 300 150 35 15	475 450 230 70 30			$I_C = -10\text{mA}, V_{CE} = -2\text{V}^*$ $I_C = -100\text{mA}, V_{CE} = -2\text{V}^*$ $I_C = -2\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -4\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -6\text{A}, V_{CE} = -2\text{V}^*$
Transition Frequency	f_T	150	180		MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}		21	30	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$
Turn-On Time	$t_{(on)}$		40		ns	$V_{CC} = -10\text{V}, I_C = -1\text{A}$ $I_{B1} = I_{B2} = 20\text{mA}$
Turn-Off Time	$t_{(off)}$		670		ns	

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

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TYPICAL CHARACTERISTICS

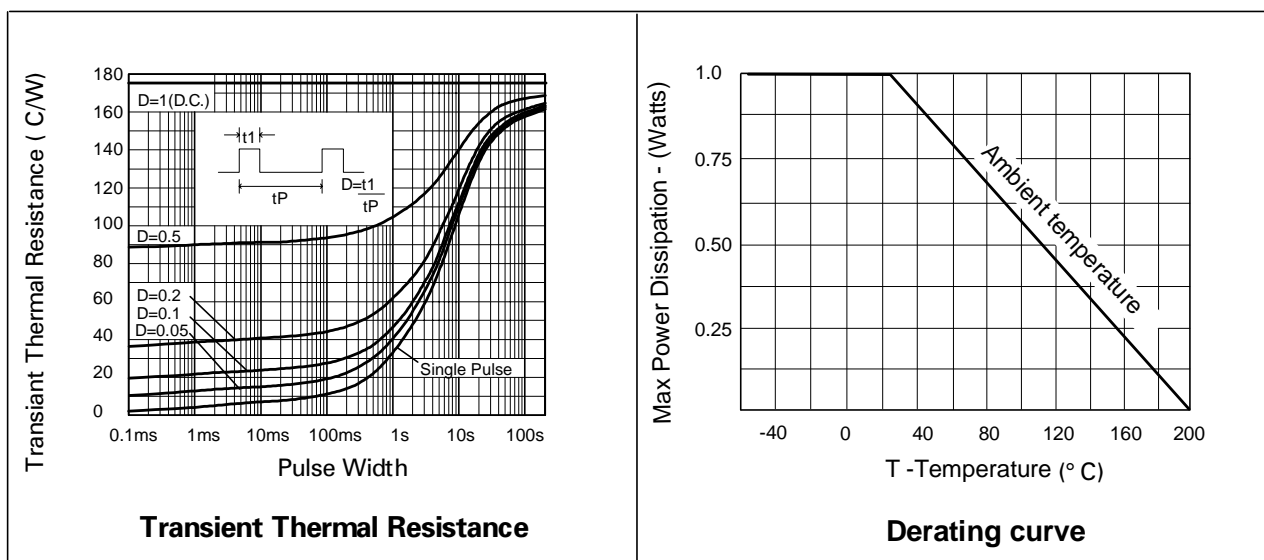


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THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient ₁	$R_{th(j-amb)1}$	175	°C/W
Junction to Ambient ₂	$R_{th(j-amb)2} †$	116	°C/W

† Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.



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